FDMS001N025DSD

PowerTrench® Power Clip

25 V Asymmetric Dual N−Channel MOSFET

General Description

This device includes two specialized N−Channel MOSFETs in a dual package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET (Q2) have been designed to provide optimal power efficiency.

Features

Q1: N−Channel

- Max $r_{DS(on)}$ = 3.25 mΩ at V_{GS} = 10 V, I_D = 19 A
- Max $r_{DS(on)}$ = 4 mΩ at V_{GS} = 4.5 V, I_D = 17 A

Q2: N−Channel

- Max $r_{DS(on)}$ = 0.92 mΩ at V_{GS} = 10 V, I_D = 38 A
- Max $r_{DS(on)}$ = 1.20 mΩ at V_{GS} = 4.5 V, I_D = 34 A
- Low Inductance Packaging Shortens Rise/Fall Times, Resulting in Lower Switching Losses
- MOSFET Integration Enables Optimum Layout for Lower Circuit Inductance and Reduced Switch Node Ringing
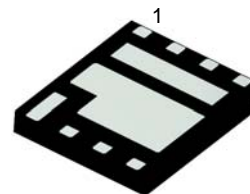- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications
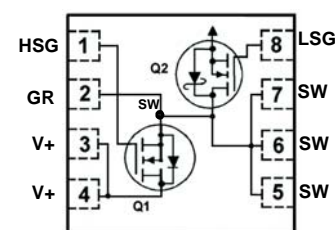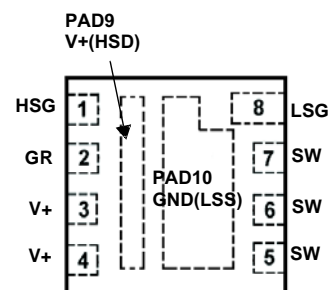
- Computing
- Communications
- General Purpose Point of Load

ON Semiconductor®

PQFN8
POWER CLIP
CASE 483AR

PIN ASSIGNMENT

Pin	Name	Description
1	HSG	High Side Gate
2	GR	Gate Return
3,4,9	V+(HSD)	High Side Drain
5,6,7	SW	Switching Node, Low Side Drain
8	LSG	Low Side Gate
10	GND(LSS)	Low Side Source

ORDERING INFORMATION

FDMS001N025DSD

Table 1. MAXIMUM RATINGS $T_A = 25°C$ unless otherwise noted

Symbol	Parameter		Q1	Q2	Units
V_{DS}	Drain to Source Voltage		25 (Note 1)	25	V
V_{GS}	Gate to Source Voltage		+16/−12V	+16/−12V	V
I_D	Drain Current −Continuous	$T_C = 25°C$ (Note 2)	69	165	A
	−Continuous	$T_C = 100°C$ (Note 2)	43	104	
	−Continuous	$T_A = 25°C$	19 (Note 7a)	38 (Note 7b)	
	−Pulsed	$T_A = 25°C$ (Note 3)	381	1240	
E_{AS}	Single Pulse Avalanche Energy	(Note 4)	121	337	mJ
P_D	Power Dissipation for Single Operation	$T_C = 25°C$	26	42	W
	Power Dissipation for Single Operation	$T_A = 25°C$	2.1 (Note 7a)	2.3 (Note 7b)	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		−55 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. The continuous V_{DS} rating is 25 V; However, a pulse of 30 V peak voltage for no longer than 100 ns duration at 600 KHz frequency can be applied.
2. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro−mechanical application board design.
3. Pulsed Id please refer to Figure 11 and Figure 24 SOA graphs for more details.
4. Q1: E_{AS} of 121 mJ is based on starting $T_J = 25°C$; N−ch: L = 3 mH, $I_{AS} = 9$ A, $V_{DD} = 25$ V. 100% tested at L = 0.1 mH, $I_{AS} = 29$ A.
   Q2: E_{AS} of 337 mJ is based on starting $T_J = 25°C$; N−ch: L = 3 mH, $I_{AS} = 15$ A, $V_{DD} = 25$ V. 100% tested at L = 0.1 mH, $I_{AS} = 48$ A.

Table 2. THERMAL CHARACTERISTICS

Symbol	Parameter	Q1	Q2	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.9	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	60 (Note 7a)	55 (Note 7b)	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	130 (Note 7c)	120 (Note 7d)	

Table 3. ELECTRICAL CHARACTERISTICS $T_J = 25°C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
OFF CHARACTERISTICS							
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 1$ mA, $V_{GS} = 0$ V	Q1	25			V
		$I_D = 1$ mA, $V_{GS} = 0$ V	Q2	25			
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 10$ mA, referenced to 25°C	Q1		15		mV/°C
		$I_D = 10$ mA, referenced to 25°C	Q2		28		
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20$ V, $V_{GS} = 0$ V	Q1			1	μA
		$V_{DS} = 20$ V, $V_{GS} = 0$ V	Q2			500	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = +16$ V/−12 V, $V_{DS} = 0$ V	Q1			±100	nA
		$V_{GS} = +16$ V/−12 V, $V_{DS} = 0$ V	Q2			±100	nA
ON CHARACTERISTICS							
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 320$ μA	Q1	0.8	1.3	2.5	V
		$V_{GS} = V_{DS}$, $I_D = 1$ mA	Q2	1.0	1.5	3.0	
$\Delta V_{GS(th)}/\Delta T_J$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 1$ mA, referenced to 25°C	Q1		−4		mV/°C
		$I_D = 10$ mA, referenced to 25°C	Q2		−3		
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10$ V, $I_D = 19$ A	Q1		2.5	3.25	mΩ
		$V_{GS} = 4.5$ V, $I_D = 17$ A			3.0	4.0	
		$V_{GS} = 10$ V, $I_D = 19$ A, $T_J = 125°C$			3.5	5.0	
		$V_{GS} = 10$ V, $I_D = 38$ A	Q2		0.70	0.92	
		$V_{GS} = 4.5$ V, $I_D = 34$ A			0.92	1.20	
		$V_{GS} = 10$ V, $I_D = 38$ A, $T_J = 125°C$			0.96	1.38	

Table 3. ELECTRICAL CHARACTERISTICS T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
ON CHARACTERISTICS							
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 19 A V_{DS} = 5 V, I_D = 38 A	Q1 Q2		98 262		S
DYNAMIC CHARACTERISTICS							
C_{iss}	Input Capacitance	Q1: V_{DS} = 13 V, V_{GS} = 0 V, f = 1 MHZ	Q1 Q2		1370 5105		pF
C_{oss}	Output Capacitance	Q2: V_{DS} = 13 V, V_{GS} = 0 V, f = 1 MHZ	Q1 Q2		625 1810		pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		44 173		pF
R_g	Gate Resistance		Q1 Q2	0.1 0.1	0.4 0.3	1.2 1.0	Ω
SWITCHING CHARACTERISTICS							
$t_{d(on)}$	Turn–On Delay Time	Q1: V_{DD} = 13 V, I_D = 19 A, R_{GEN} = 6 Ω	Q1 Q2		8 15	16 26	ns
t_r	Rise Time	Q2: V_{DD} = 13 V, I_D = 38 A, R_{GEN} = 6 Ω	Q1 Q2		2 5	10 10	ns
$t_{d(off)}$	Turn–Off Delay Time		Q1 Q2		22 39	34 62	ns
t_f	Fall Time		Q1 Q2		2 4	10 10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V	Q1 V_{DD} = 13 V, I_D = 19 A	Q1 Q2		21 75	30 104	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V	Q2 V_{DD} = 13 V, I_D = 38 A	Q1 Q2		9.7 35	14 49	nC
Q_{gs}	Gate to Source Gate Charge		Q1 Q2		2.9 12		nC
Q_{gd}	Gate to Drain "Miller" Charge		Q1 Q2		2.0 7.9		nC
DRAIN–SOURCE DIODE CHARACTERISTICS							
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 19 A (Note 6) V_{GS} = 0 V, I_S = 38 A (Note 6)	Q1 Q2		0.8 0.8	1.2 1.2	V
I_S	Diode continuous forward current	T_C = 25°C (Note 2)	Q1 Q2			69 125	A
$I_{S,Pulse}$	Diode pulse current	T_C = 25°C (Note 3)	Q1 Q2			381 1240	A
t_{rr}	Reverse Recovery Time	Q1 I_F = 19 A, di/dt = 100 A/μs	Q1 Q2		27 39	44 62	ns
Q_{rr}	Reverse Recovery Charge	Q2 I_F = 38 A, di/dt = 300 A/μs	Q1 Q2		12 55	21 87	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
5. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR–4 material. $R_{\theta CA}$ is determined by the user's board design.
6. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

PACKAGE MARKING AND ORDERING INFORMATION

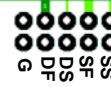| Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS001N025DSD	FDMS001N025DSD	Power Clip 56	13"	12 mm	3000 units
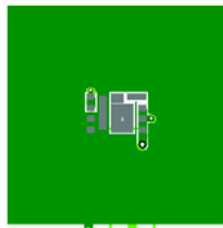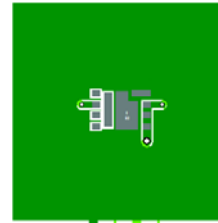
(Note 7a)

(Note 7b)

(Note 7c)

(Note 7d)

7. a) 60°C/W when mounted on a 1 in² pad of 2 oz copper
   b) 55°C/W when mounted on a 1 in² pad of 2 oz copper
   c) 130°C/W when mounted on a minimum pad of 2 oz copper
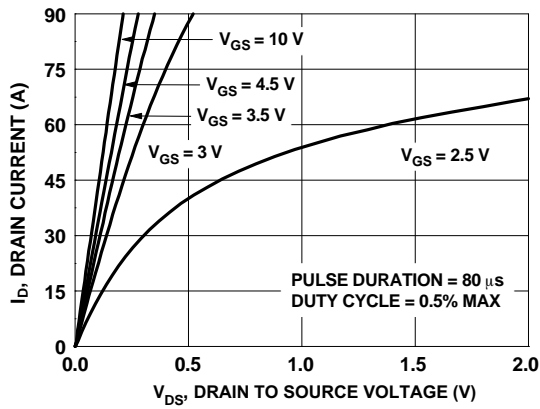   d) 120°C/W when mounted on a minimum pad of 2 oz copper

TYPICAL CHARACTERISTICS (Q1 N–Channel) T_J = 25°C unless otherwise noted
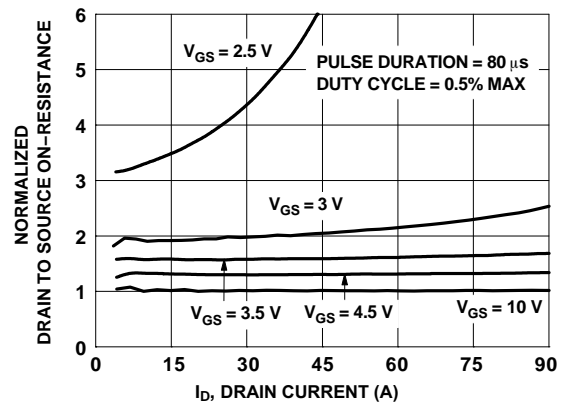

Figure 1. On Region Characteristics

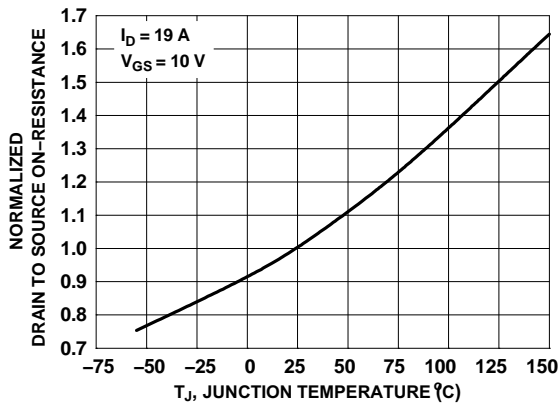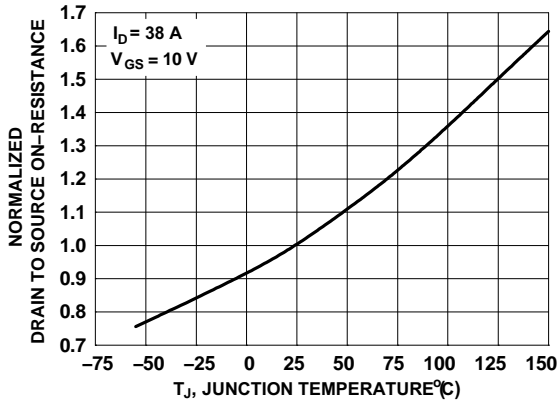Figure 2. Normalized On–Resistance vs. Drain Current and Gate Voltage

Figure 3. Normalized On Resistance vs. Junction Temperature
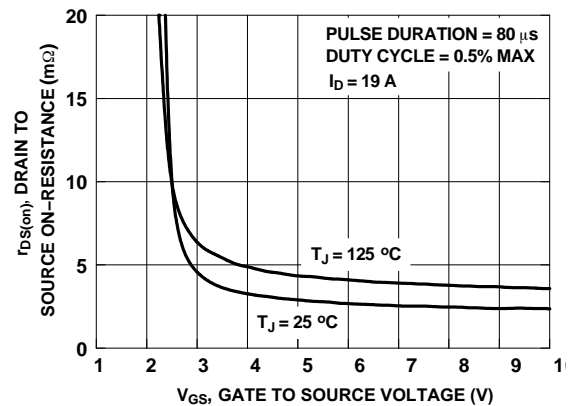
Figure 4. On–Resistance vs. Gate to Source Voltage
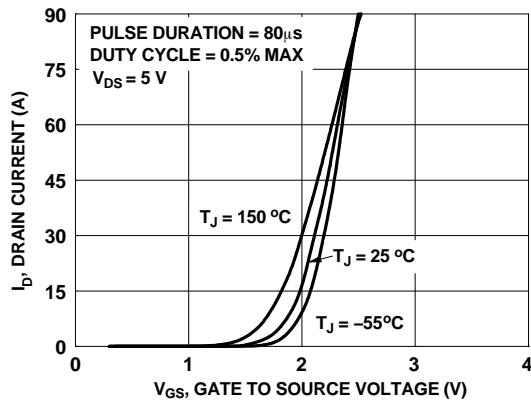
Figure 5. Transfer Characteristics
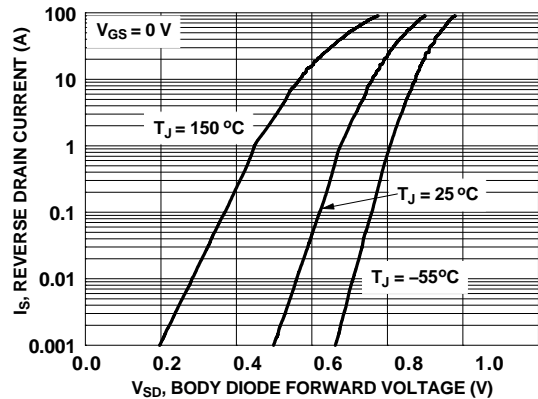
Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

FDMS001N025DSD
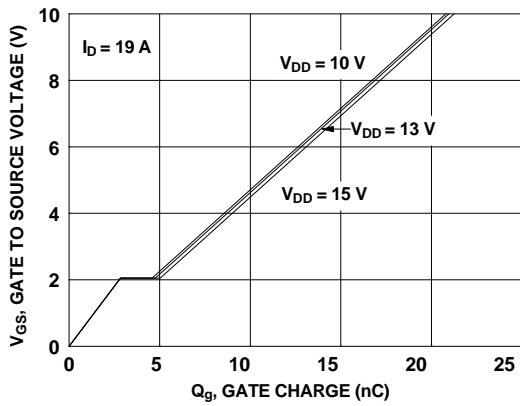
Figure 7. Gate Charge Characteristics
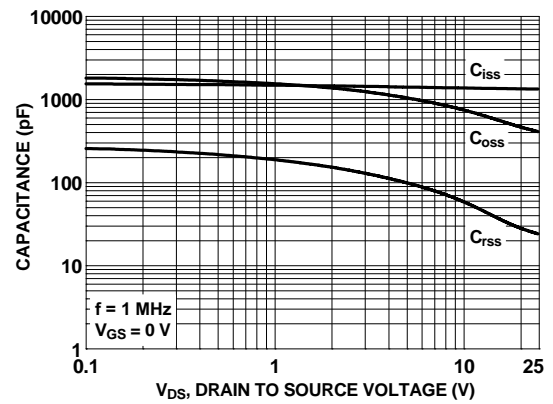
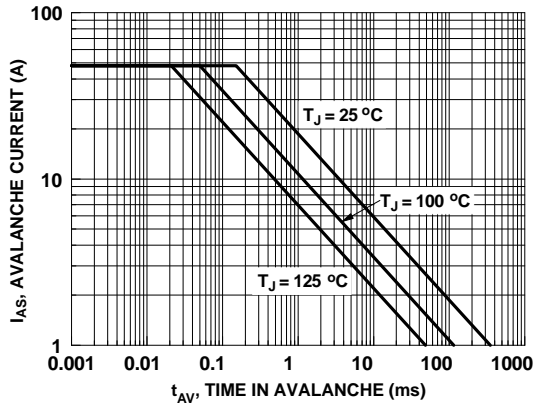**Figure 8. Capacitance vs. Drain to Source Voltage**
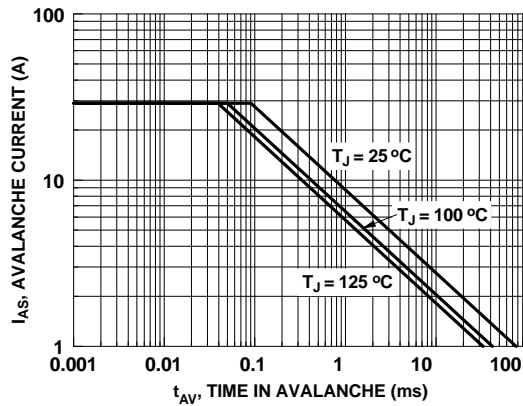
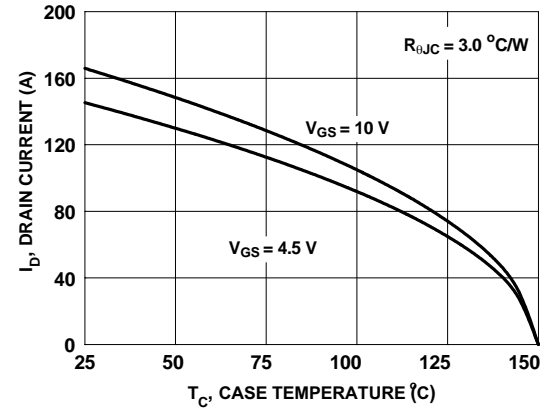**Figure 9. Unclamped Inductive Switching Capability**
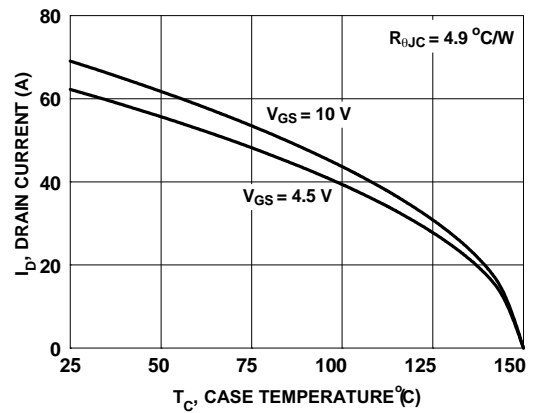
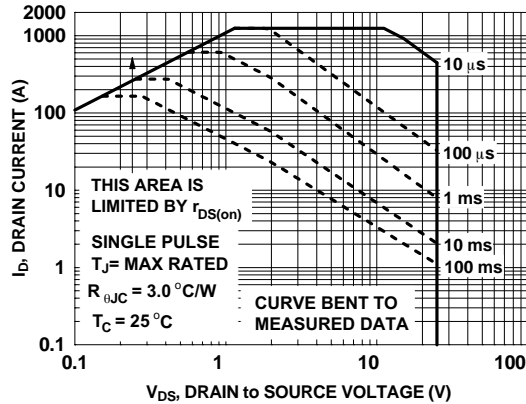**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**
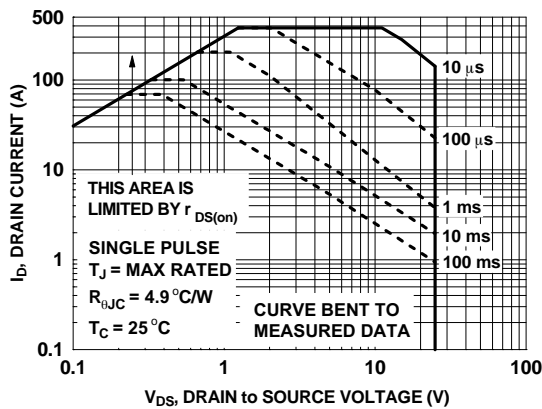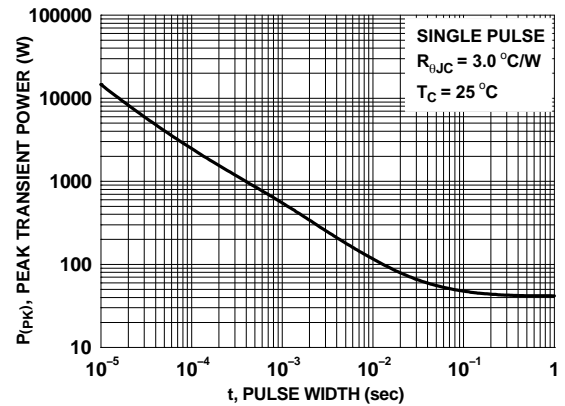

Figure 11. Forward Bias Safe Operating Area
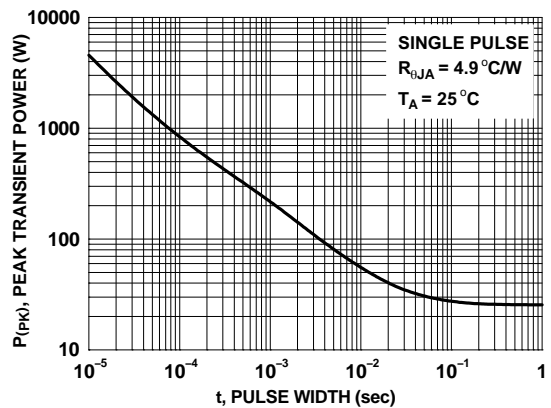

Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (Q1 N–Channel) $T_J = 25°C$ unless otherwise noted
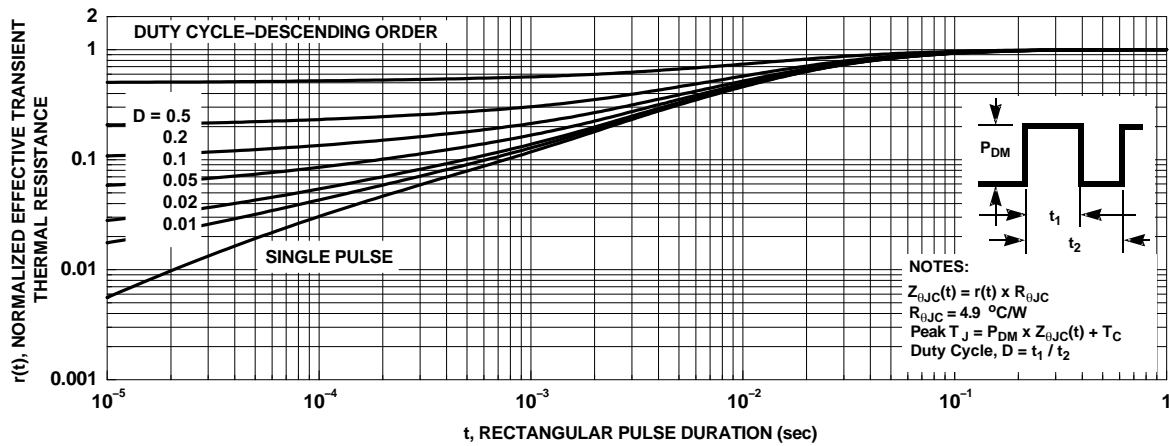
Figure 13. Junction–to–Case Transient Thermal Response Curve

NOTES:
$Z_{\theta JC}(t) = r(t) \times R_{\theta JC}$
$R_{\theta JC} = 4.9 \ °C/W$
Peak $T_J = P_{DM} \times Z_{\theta JC}(t) + T_C$
Duty Cycle, $D = t_1 / t_2$

DUTY CYCLE–DESCENDING ORDER

D = 0.5
0.2
0.1
0.05
0.02
0.01

SINGLE PULSE

TYPICAL CHARACTERISTICS (Q2 N–Channel) T_J = 25°C unless otherwise noted

Figure 14. On Region Characteristics
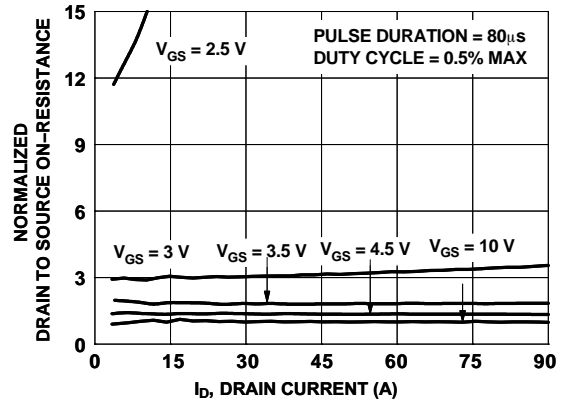
Figure 15. Normalized On–Resistance vs. Drain Current and Gate Voltage

Figure 16. Normalized On Resistance vs. Junction Temperature
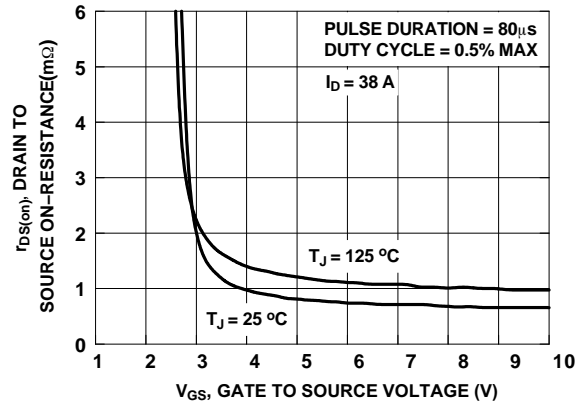
Figure 17. On–Resistance vs. Gate to Source Voltage
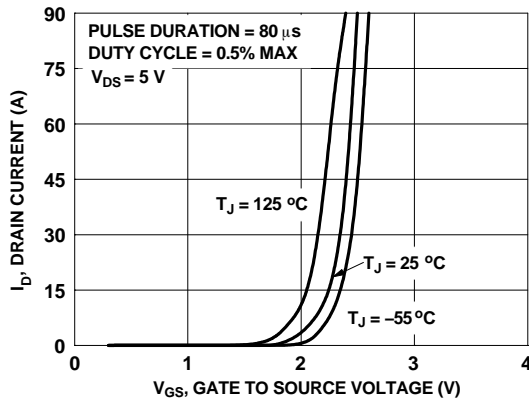
Figure 18. Transfer Characteristics
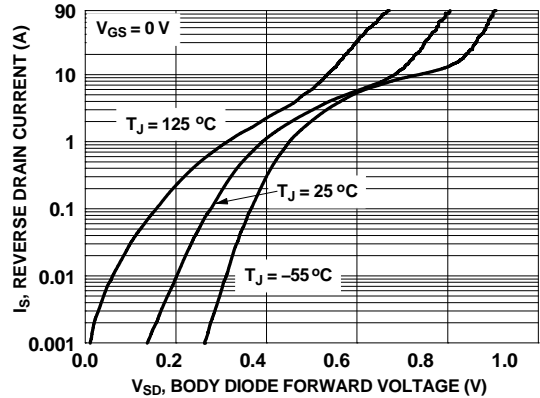
Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

FDMS001N025DSD
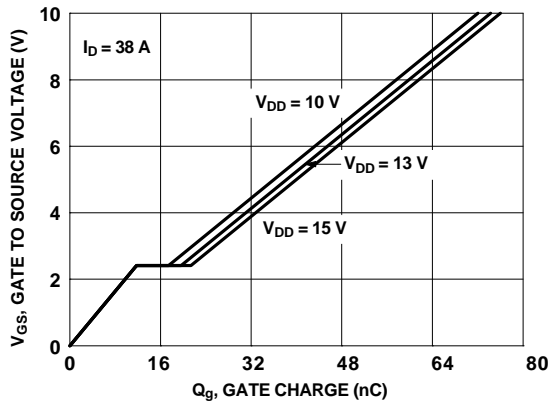
Figure 20. Gate Charge Characteristics
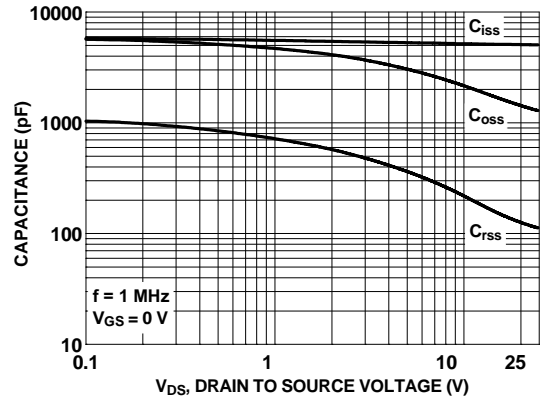
Figure 21. Capacitance vs. Drain to Source Voltage

Figure 22. Unclamped Inductive Switching Capability

Figure 23. Maximum Continuous Drain Current vs. Case Temperature

Figure 24. Forward Bias Safe Operating Area

Figure 25. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (Q2 N−Channel) T_J = 25°C unless otherwise noted
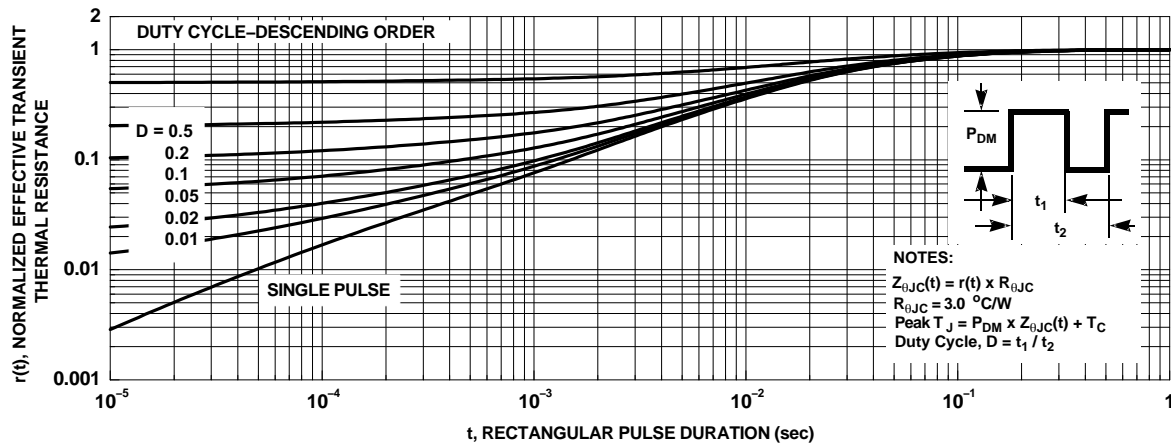
Figure 26. Junction−to−Case Transient Thermal Response Curve

TYPICAL CHARACTERISTICS (continued)

ON Semiconductor's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 27 shows the reverses recovery characteristic of the FDMS001N025DSD.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.
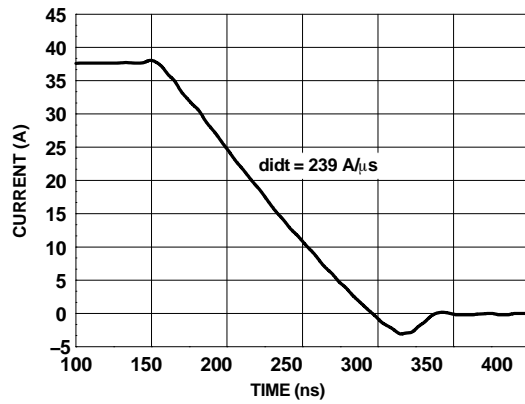
Figure 27. FDMS001N025DSD SyncFET Body Diode Reverse Recovery Characteristic
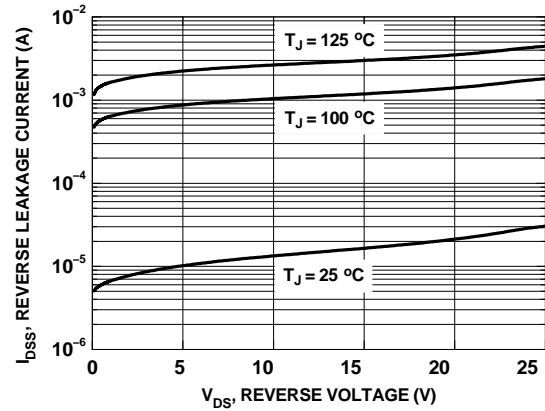
Figure 28. SyncFET Body Diode Reverse Leakage vs. Drain–Source Voltage

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onsemi
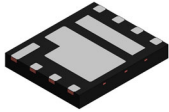
PQFN8 5.00x6.00x0.75, 1.27P
CASE 483AR
ISSUE D

DATE 06 NOV 2023

TOP VIEW

PIN 1 INDICATOR

DETAIL A
(SCALE: 2X)

SEATING PLANE

SEE DETAIL A

SIDE VIEW

BOTTOM VIEW

RECOMMENDED LAND PATTERN

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.
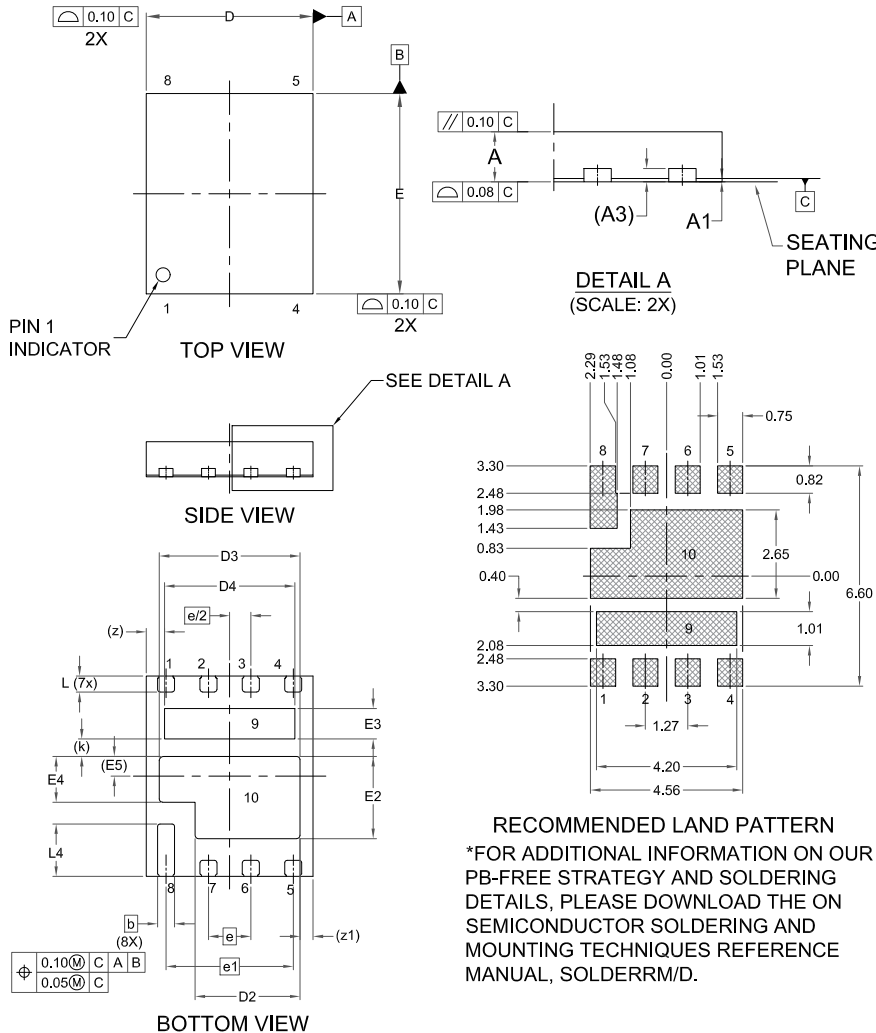
NOTES: UNLESS OTHERWISE SPECIFIED

A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229, DATED 11/2001.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.20 REF		
b	0.51 BSC		
D	4.90	5.00	5.10
D2	3.05	3.15	3.25
D3	4.12	4.22	4.32
D4	3.80	3.90	4.00
E	5.90	6.00	6.10
E2	2.36	2.46	2.56
E3	0.81	0.91	1.01
E4	1.27	1.37	1.47
E5	0.59 REF		
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
k	0.52 REF		
L	0.38	0.48	0.58
L4	1.47	1.57	1.67
z	0.55 REF		
z1	0.39 REF		

DOCUMENT NUMBER:	98AON13666G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	PQFN8 5.00x6.00x0.75, 1.27P		PAGE 1 OF 1

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ADDITIONAL INFORMATION

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